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## TABLE OF CONTENTS

3D Heterogeneous Integration (3DHI): An Enabler for Next Generation RF Systems .....	1
<i>Thomas Kazior, Sharon Woodruff, Gregory Jones, Iskren Abdomerovic</i>	
Practical Approaches to Industrializing Near-THz Communication Systems .....	5
<i>Shahriar Shahramian, Mustafa Sayginer, Michael Holyoak, Mohamed Elkhoully, Mike Zierdt, Jaegeun Ha, Joe Weiner, Yves Baeyens</i>	
A Novel Base Resistance Model Incorporating Base Distributive Effects Along with Emitter Length.....	9
<i>Bin Li, Andre G. Metzger, Cristian Cismaru, Yingying Yang</i>	
Physics-Based Compact Modeling of the Transfer Current in III-V DHBTs with the Generalized Integral Charge Control Relation.....	12
<i>Markus Müller, Mario Krattenmacher, Hendrik Leenders, Sara Hamzeloui, Colombo Bolognesi, Christoph Jungemann, Michael Schröter</i>	
Practical and Efficient Approaches to Device Modeling and Power Amplifier Module Design .....	16
<i>Hans Rohdin, Bart Jansen, William Snodgrass, J. Stephen Kofol, Sonja Nedeljkovic, Ziad El Chami, Will Sutton, Tom Dungan</i>	
Thermal Characterization of InP/GaAsSb DHBTs: Effect of Emitter and Collector Layers.....	24
<i>F. Ciabattini, A. M. Arabhavi, S. Hamzeloui, M. Ebrahimi, O. Ostinelli, C. R. Bolognesi</i>	
A 12 Bit R-2R Digital-To-Analog Converter for Shuttling Operation in a Trapped-Ion Quantum Computer.....	28
<i>Alexander Meyer, Peter Toth, Axel Engelhardt, Jens Repp, Matthias Brand, Vadim Issakov</i>	
Vertical Power Delivery and Heterogeneous Integration for High-Performance Computing.....	32
<i>Hanh-Phuc Le, Casey Hardy, Hieu Pham, Mohamed Mehdi Jatlaoui, Frederic Voiron, Patrick Mercier, Po-Han Chen, Saket Jha</i>	
A Circuit Designer's Perspective on Transistor Modelling Challenges for 6G, Fiberoptics, and Quantum Computing ICs.....	36
<i>S. P. Voinigescu, S. Bonen, S. Pati Tripathi, S. Bagchi, G. Cooke, T. Jager, A. Bharadwaj, J. Zhao</i>	
Electro-Thermal Investigation of SiGe HBTs: A Review .....	44
<i>Thomas Zimmer, Sébastien Fregonese, Anjan Chakravorty</i>	
Simulation of DC Safe Operating Area and RF Breakdown in SiGe PA HBT .....	50
<i>Beng Woon Lim, Ajay Raman, Saurabh Sirohi</i>	
A Physically-Based Matching Model for HiSIM_HV .....	54
<i>Rachid Hamani, J. R. O. R. Martins, Hagen Wald, Joerg Gessner, Michaelina Ong Ing Ing</i>	
Cryogenic Modeling for Open-Source Process Design Kit Technology .....	58
<i>Akin Akturk, Ayushman Tripathi, Mehdi Saligane</i>	
Flipchip Characterization for RF SOI Switch Model Improvement.....	66
<i>Kathleen Muhonen, Jayashree Jayabalan, Scott Parker</i>	

A 33 dBm, >30% PAE GaN Power Amplifier Based on a Sub-Quarter-Wavelength Balun for 5G Applications.....	70
<i>Dongyang Yan, Yang Zhang, Dries Peumans, Mark Ingels, Piet Wambacq</i>	
A 4–18 GHz, 35 W GaN MMIC Power Amplifier with Improved Thermal Performance .....	74
<i>Michael Litchfield, Andrew Kingswood</i>	
Fully Qualified Gallium Nitride Power Amplifier for Use in Ka-Band Commercial Space Applications.....	78
<i>Simon Mok, Norman Chiang, Vivian Law, James J. Sowers</i>	
Transient Field-Plate Thermometry in Cascode FET Power Amplifiers .....	82
<i>David J. Niven, Simon J. Mahon, Andrew J. Jones, Melissa C. Gorman</i>	
A Compact 0.98 THz Source with On-Chip Antenna in 250-Nm InP DHBT .....	86
<i>Senne Gielen, Yang Zhang, Mark Ingels, Patrick Reynaert</i>	
Analog/mmWave Circuit Demonstrations in State-Of-The-Art SiGe BiCMOS Process for 5G and Optical Transceivers .....	90
<i>Venkata Vanukuru, Hari Kakara, Santosh Gedela, Vaibhav Ruparelia, Prateek Kumar Sharma</i>	
D-Band Power Amplifier with 27 dBm Peak Output Power and 14.9% PAE in 250-Nm InP HBT Technology .....	94
<i>Amirreza Alizadeh, Utku Soylu, Navneet Sharma, Gary Xu, Mark J. W. Rodwell</i>	
A High Linearity SiGe D-Band Diode Ring Mixer .....	98
<i>Olga Krylova, Jan Schopf, Klaus Aufinger, Nils Pohl</i>	
A Ka-Band VCO Chip with Integrated Dividers Using 1.5 V Supply in 130-Nm SiGe BiCMOS Technology for Low-Power Radar Sensors.....	102
<i>Batuhan Sutbas, Mohamed Hussein Eissa, Gerhard Kahmen</i>	
Demonstration of a Ku-Band N-Path Downconverter in GaN-On-SiC.....	106
<i>Damla Dimlioglu, Alyosha C. Molnar</i>	
Gen1 Active Tunable SiGe Integrated Parallel Synthesis Filters (PSF) Without Q-Enhancement.....	110
<i>Farooq Amin, Shuai Zhou, Long Huang, Christopher Latorre, Folu Popoola, Parrish Ralston</i>	
Wideband Switched-Capacitor and Switched-Transmission-Line Circulators in 40nm GaN Technology: Design and Device Modeling .....	114
<i>Hari Vemuri, Armagan Dascurcu, Kexin Li, Harish Krishnaswamy</i>	
Adaptable 40 nm GaN T-Gate MMIC Processes for Millimeter-Wave Applications.....	118
<i>D. Denninghoff, E. Arkun, J.-S. Moon, H. Tran, A. Corrion, G. Siddiqi, D. Fanning, M. Fireman, J. Tai, J. Wong, B. Grabar, C. Dao, I. Milosavljevic, R. Tran, A. Getter, A. Clapper, S. Dadafshar, J. Georgieva, H. Moyer, N. Miller, M. Elliott, R. Gilbert</i>	
Microstrip and Grounded CPW Calibration Kit Comparison for On-Wafer Transistor Characterization from 220 GHz to 325 GHz.....	124
<i>Rob D. Jones, Jerome Cheron, Bryan T. Bosworth, Benjamin F. Jamroz, Dylan F. Williams, Miguel E. Urteaga, Ari D. Feldman, Peter H. Aaen</i>	
On Extracting the Maximum Power Density at High Frequencies from Gallium Nitride and Related Materials.....	128
<i>Mohamadali Malakoutian, Srabanti Chowdhury</i>	

AlScN High Electron Mobility Transistors: Integrating High Piezoelectric, High K Dielectric, and Ferroelectric Functionality .....	132
<i>Joseph Casamento, Kazuki Nomoto, Thai-Son Nguyen, Hyunjea Lee, Chandrasekhar Savant, Lei Li, Austin Hickman, Takuya Maeda, Yu-Tsun Shao, Jimmy Encomendero, Ved Gund, Timothy Vasen, Shamima Afroz, Daniel Hannan, David A. Muller, Huili Grace Xing, Debdeep Jena</i>	
High Performance 0.25 $\mu$ m GaN Technology with Low Memory Effects .....	137
<i>B. Grote, B. Green, C. Gaw, Y. Wei, D. Hill, P. Renaud, J. Wan, C. Rampley, D. Burdeaux, K. Foxx, M. Vadipour, D. Currier, C. Zhu, H. Kabir, T. Arnold, H. Stewart, D. Ferguson, J. Higginbottom, P. Hu</i>	
Millimeter-Wave Gallium Nitride Maturation of 40nm T3 Gallium Nitride Monolithic Microwave Integrated Circuit Process.....	141
<i>David Fanning, Andrea Corrion, Georges Siddiqi, Souheil Nadri, Dan Denninghoff, Erdem Arkun, Sadaf Dadafshar, Ignacio Ramos, Harris Moyer, Andy Fu, John Carlson, Shyam Bharadwaj</i>	
Multi-Finger 250-Nm InP/GaAsSb DHBTs with Record 37.3 % Class-A PAE at 94 GHz .....	145
<i>Sara Hamzeloui, Akshay M. Arabhavi, Filippo Ciabattini, Mojtaba Ebrahimi, Markus Müller, Olivier Ostinelli, Michael Schröter, Colombo R. Bolognesi</i>	
100 GBaud DSP-Free PAM-4 Optical Signal Generation Using an InP-DHBT AMUX-Driver and a Thin-Film Lithium Niobate Modulator Assembly.....	149
<i>R. Hersent, F. Jorge, F. Blache, B. Duval, M. Goix, H. Mardoyan, S. Almonacil, M. Xu, Y. Zhu, L. Chen, Z. Hu, J. Renaudier, M. Riet, A. Konczykowska, B. Ardouin</i>	
High-Speed SiGe BiCMOS Circuits for Optical Communication .....	153
<i>Guy Torfs, Bart Moeneclaey, Joris Lambrecht, Cedric Bruynsteen, Jakob Declerq, Shengpu Niu, Nishant Singh, Marijn Verbeke, Xin Yin, Peter Ossieur, Johan Bauwelinck</i>	
A 19-DB Peaking at 72-GHz and 4.1-Vppd Output Swing SiGe BiCMOS Linear Driver with Dynamic Cascode Output Buffer.....	159
<i>Hiroshi Uemura, Taichi Misawa, Naoki Itabashi, Munetaka Kurokawa, Yoshiyuki Sugimoto, Seiji Kumagai, Masaru Takechi, Keiji Tanaka</i>	
A Shunt-Feedback TIA with Common-Base Variable Gain Input Stage for 128-GBaud Coherent Communication .....	163
<i>Seiji Kumagai, Yoshiyuki Sugimoto, Hiroshi Uemura, Munetaka Kurokawa, Naoki Itabashi, Masaru Takechi, Takuya Okimoto, Keiji Tanaka</i>	
Design Trade-Offs Between Series-Peaking Inductor and High $f_T$ SiGe HBTs in Transimpedance Amplifiers.....	167
<i>Prateek Kumar Sharma, Vaibhav Ruparelia, Saurabh Sirohi, Uppili S. Raghunathan, Venkata Vanukuru, Vibhor Jain</i>	
A 12–162 GHz Distributed Amplifier in a 45-Nm BiCMOS SOI Process Achieving 2.67 THz Gain-Bandwidth Using an Active Bias Termination.....	171
<i>Justin J. Kim, Wonho Lee, James F. Buckwalter</i>	
A 15–24 GHz, 15W Reactively Matched GaN MMIC Power Amplifier .....	175
<i>Michael Litchfield</i>	
An 18.6-DBm, 8-Way-Combined D-Band Power Amplifier with 21.6% PAE in 22-Nm FD-SOI CMOS.....	179
<i>Jeff Shih-Chieh Chien, Eythan Lam, James F. Buckwalter</i>	

D-Band 4-Ch Antenna-On-Chip Phased-Array TX Front-End.....	183
<i>Toshihide Kuwabara, Naoki Oshima, Koki Tanji, Noriaki Tawa, Shinji Hachiyama, Tomoya Kaneko</i>	
Low-Noise Si/SiGe HBT for LEO Satellite User Terminals in Ku-Ka Bands .....	187
<i>A. Gauthier, E. Brezza, A. Montagné, N. Guitard, J. Azevedo Goncalves, M. Buczko, S. Jan, N. Derrier, D. Céli, C. Deglise-Favre, J. Ma, H. Audouin, F. Deprat, I D. Ristoiu, L. Berthier, L. Clément, B. Grelaud, C. Rougier, P. Chevalier</i>	
A 28-Gb/s 27.2mW NRZ Full-Rate Bang-Bang Clock and Data Recovery in 22 nm FD-SOI CMOS Technology .....	191
<i>Mohammed Ifekhar, Harshan Gowda, Pascal Kneuper, Babak Sadiye, Wolfgang Mueller, J. Christoph Scheytt</i>	
A DC-To-150-GHz InP-DHBT Active Combiner Module for Ultra-Broadband Signal Generation.....	195
<i>Teruo Jyo, Munehiko Nagatani, Miwa Mutoh, Yuta Shiratori, Hitoshi Wakita, Hiroyuki Takahashi</i>	
An 80-GBaud PAM-4 $G_m$ -Boosted Variable-Gain TIA in 22-nm FDSOI .....	199
<i>Jianan Zhao, Sorin P. Voinigesu</i>	
Low Phase Noise and Low Power Consumption Magnetic Cross-Coupled Push-Push VCO in SiGe BiCMOS Technology .....	203
<i>Shuvadip Ghosh, Hao Li, Nils Pohl</i>	
Quad-Channel 100-GHz-Bandwidth InP- HBT-Based Linear Amplifier Module for High Symbol Rate Communications .....	207
<i>Hitoshi Wakita, Teruo Jyo, Munehiko Nagatani, Hiroyuki Takahashi</i>	
46–102 GHz GaN Balanced Cascode Amplifier-Isolator .....	211
<i>Anthony Romano, Timothy Sonnenberg, Zoya Popovic</i>	
A Wideband Ultra-Low Noise 15–55 GHz Dual-Beam Receive Phased-Array Beamformer with 2.9-4.2 dB NF.....	215
<i>Omar Hassan, Mir Mahmud, Abdulrahman Alhamed, Gabriel M. Rebeiz</i>	
Advanced mHEMT Technologies for Use in Radar, Communication and Meteorological Applications.....	219
<i>Axel Tessmann, Arnulf Leuther, Fabian Thome, Laurenz John, Bersant Gashi, Hermann Massler, Alexander Saam, Sebastien Chartier</i>	
GaN/Si 37–40 GHz T/R Chip MMIC for 5G Communications .....	225
<i>M. El Kaamouchi, A. Gasmi, B. Wroblewski, R. Leblanc, J. Poulain, P. Altuntas</i>	
120 GHz GaAs Single-Balanced Mixer .....	229
<i>Nethini Weerathunge, Simon J. Mahon, Gerry McCulloch, Sudipta Chakraborty</i>	
A 377–416 GHz Push-Push Frequency Doubler with Driving Stage and Transformer-Based Mode Separation in SiGe BiCMOS .....	233
<i>Justin Romstadt, Tobias Welling, Florian Vogelsang, Muhammed Ali Yildirim, Klaus Aufinger, Nils Pohl</i>	
A 61-187.2-GHz Traveling Wave Push-Push Frequency Doubler in a 130 nm SiGe:C BiCMOS Technology with 101.7% Fractional Bandwidth .....	237
<i>Melika Dedovic, Florian Vogelsang, Hakan Papurcu, Klaus Aufinger, Nils Pohl</i>	

A D-Band Sub-Harmonically Pumped Mixer with High LO Suppression Using 250-Nm InP DHBT P-N Junction .....	241
<i>Shinji Hachiyama, Koki Tanji, Toshihide Kuwabara, Naoki Oshima, Kazuaki Kunihiro, Tomoya Kaneko</i>	
Electrostatic Discharge Stress Effects on the Performance and Reliability of High Performance NPN SiGe HBTs .....	245
<i>Dimitris P. Ioannou, Ephrem Gebreselasie, Vinh Pham, Uppili S. Raghunathan</i>	
Numerical Device Simulation Aided Study of RF-Stress-Caused Degradation in SiGe HBTs .....	249
<i>Christoph Weimer, Viktor Kazantsev, Markus Maller, Michael Schroter</i>	
The Effects of Carbon Doping on the Performance and Electrical Reliability of SiGe HBTs .....	253
<i>Harrison P. Lee, Nelson E. Sepulveda-Ramos, Jeffrey W. Teng, Jackson P. Moody, Delgermaa Nergui, Brett L. Ringel, Zachary R. Brumbach, Alizeh Premani, Uppili S. Raghunathan, Vibhor Jain, John D. Cressler</i>	
High Volume Wafer Fab Equipment for RF Technologies .....	257
<i>Mike Peters, David A. Britz, Miao-Chun Chen, Manish Hemkar, Andy Lo</i>	
Monolithic Silicon Photonics .....	263
<i>T. Letavic, Massimo Sorbara, Ken Geiwont, Yusheng Bian, Vibhor Jain, Sameer Jain, Koushik Ramachandran, Zhuo-Jie Wu, Brittany Hedrick, Kevin K. Dezfulian, Yarong Lin, Teck Jung Tang, Thomas Houghton, Daniel Fisher, Takako Hirokawa, Monica Esopi, Vaishnavi Karra, Won Suk Lee, Michelle Zhang, Ryan Sporer Jorge Lubguban, Jae Kyu Cho, Rongtao Cao, Hanyi Ding, Sujith Chandran, Michal Rakowski, Abdelsalam Aboketaf, Subramanian Krishnamurthy, Scott Mills, Norman Robson, Ian Melville, Robert Fox, Vikas Gupta, Anthony Yu</i>	
The Impact of BEOL Stress on SiGe HBTs at Cryogenic Temperatures .....	270
<i>Jackson P. Moody, Jeffrey W. Teng, John D. Cressler</i>	
The SiGe HBT at Cryogenic Temperatures .....	274
<i>John D. Cressler</i>	
A 202 GHz Link Using Planar Transceiver Modules .....	280
<i>Utku Soyly, Amirreza Alizadeh, Munkyo Seo, Ahmed S. H. Ahmed, Mark J. W. Rodwell</i>	
Multi-Channel PA, LNA, and Switch MMICs for Beam-Switching Applications at 160 GHz, Based on an InGaAs mHEMT Technology .....	284
<i>Laurenz John, Thomas Merkle, Arnulf Leuther, Jaehoon Chung</i>	
Single-Ended Resistive Down-Converter MMICs in InGaAs mHEMT and GaN-HEMT Technologies for D-Band (110–170 GHz) Applications .....	288
<i>Cristina Maurette-Blasini, Rainer Weber, Sandrine Wagner, Dirk Schwantuschke, Sebastien Chartier, Rudiger Quay</i>	
Comparative Performance of 100–200 GHz Wideband Transceivers: CMOS Vs Compound Semiconductors .....	292
<i>Ethan Chou, Hesham Beshary, Meng Wei, Rami Hijab, Farhana Sheikh, Steven Callender, Ali M. Niknejad</i>	
GaN and GaAs HEMT Channel Charge Model for Nonlinear Microwave and RF Applications .....	300
<i>Anthony E. Parker, Simon J. Mahon</i>	

Modeling and Simulation of Discrete Silicon Carbide Integrated Passive Devices in High-Power RF Amplifiers .....	304
<i>Marvin Marbell, Yueying Liu, Michelle Tran, Haedong Jang, Mehdi Hasan, Dan Etter, Dan Namishia, Dan Stasiw, Jeremy Fisher, Scott T. Sheppard, Basim Noori</i>	
Modeling of the Snappy, and Soft Reverse Recovery of SiC MOSFET's Body Diode .....	310
<i>Arman Ur Rashid, Britt Brooks, Steven Manz, Daniel J. Lichtenwalner, Sei-Hyung Ryu</i>	
Optimization of GaN HEMTs with ScAlN Barrier for High 2DEG Density and Low on-Resistance .....	314
<i>Ivan Berdalovic, Mirko Poljak, Tomislav Suligoj</i>	

**Author Index**